

# Metal-Insulator Transitions in Two Dimensions: Quantum Monte Carlo Studies

- Experimental and Theoretical Motivation
- The Hubbard Model
- Quantum Simulation Techniques
- 2D Superconductor – Insulator Transitions
- 2D Metal – Anderson Insulator Transitions
- 2D Metal – Mott Insulator Transitions
- Field – Tuned Transitions
- Conclusions



UC DAVIS



## Collaborators

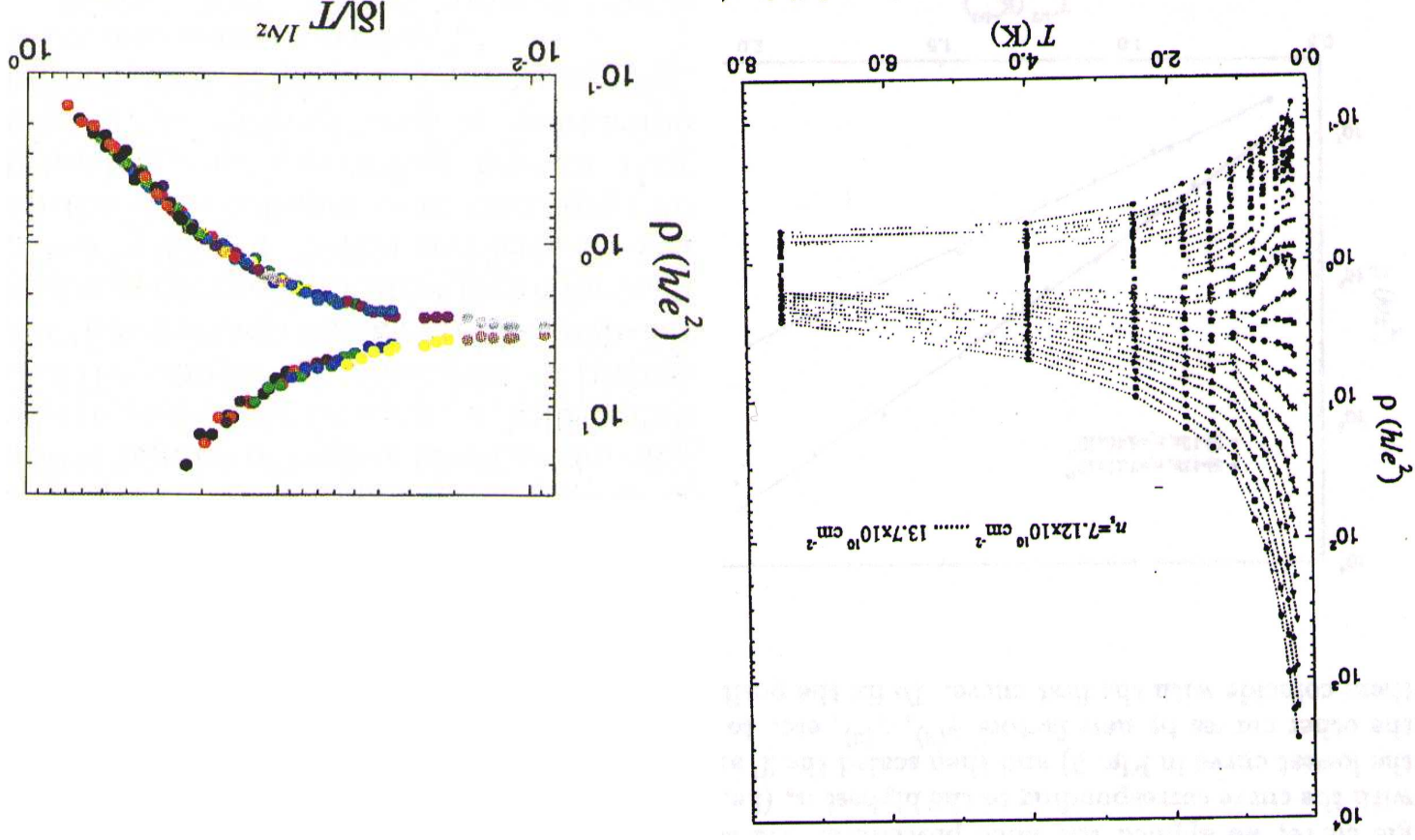
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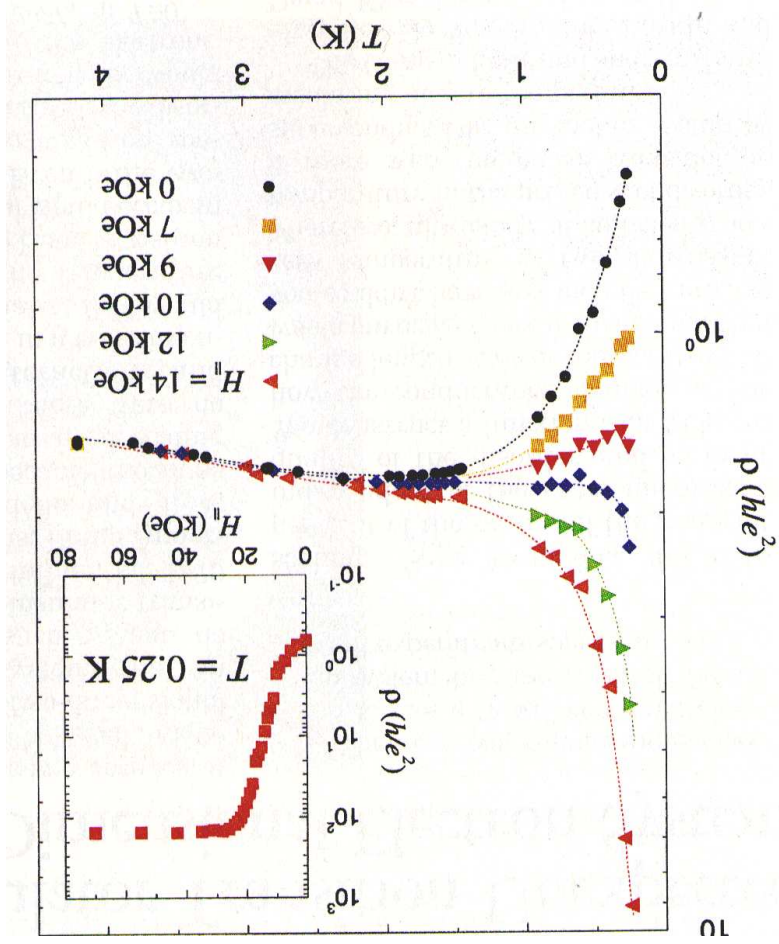
## Experimental Motivation

High mobility silicon MOSFETs show evidence for MIT. Kravchenko *et al* (1994)



Scaling behavior strengthens case for separate metal/insulator phases.

Associated scaling plots again suggest MIT.



Simonian *etal* (1997)

Similar experiments at fixed carrier density but varying magnetic field:

## Theoretical Motivation

Scaling theory of Localization (1979)

Enhanced backscattering from static impurities  
No quantum diffusion in two dimensions

Assumes no electron-electron interactions

Later perturbative RG theories (1980's)

Incorporate electron-electron interactions and disorder  
Metallic phase possible

Interaction parameter scales to strong coupling

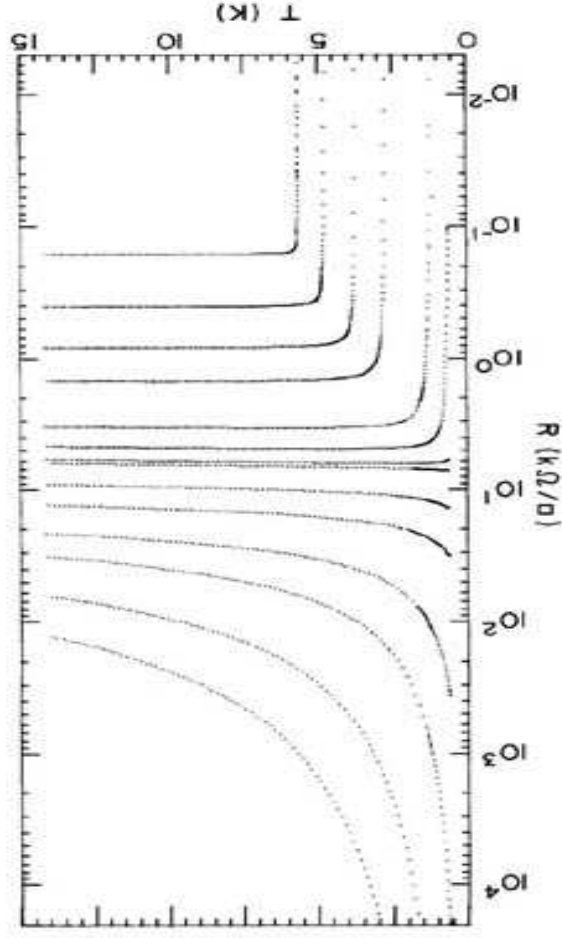
Quantum Monte Carlo

Incorporates electron-electron interactions and disorder *exactly*  
Finite size lattices: several hundred  $e^-$   
Finite temperature  $T > 0.02W$

Superconductor-Insulator Transitions

Actually, QMC first used to study SC – I rather than MIT  
Well defined thermodynamic order parameter  $\rho_s$   
No restriction on temperature  $T$  in simulations

Sheet Resistance of Bismuth Films  
Thicknesses 4.36 Å (top curve) to 74.27 Å (bottom curve)  
Y. Liu *et al* (1991)



# HUBBARD HAMILTONIAN

$$- \sum_{\langle i,j \rangle \sigma} t_{ij} (c_{i\sigma}^\dagger c_{j\sigma} + c_{j\sigma}^\dagger c_{i\sigma})$$

Kinetic Energy

$$+1 - \Delta_t > t_{ij} > +1 + \Delta_t$$

$$+ \sum_i \epsilon_i (n_{i\downarrow} + n_{i\uparrow})$$

Chemical Potential

$$- \Delta_\mu > \epsilon_i > +1 + \Delta_\mu$$

$$+U \sum_i (n_{i\downarrow} - \frac{1}{2}) (n_{i\uparrow} - \frac{1}{2})$$

Interaction Energy

$$U > 0: \text{attractive}$$

$$U < 0: \text{repulsive}$$

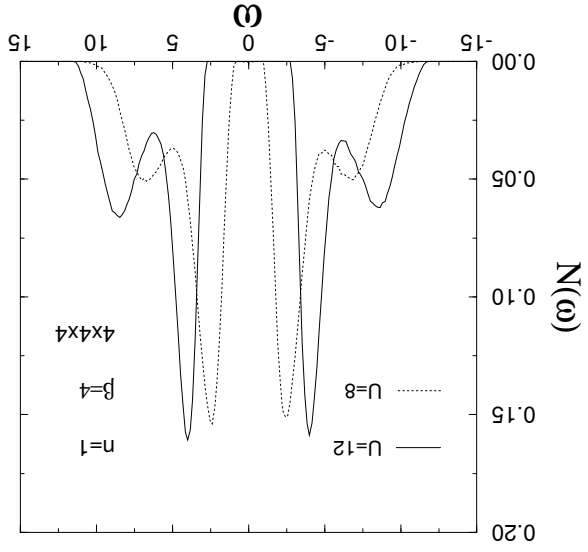
$$+B_{\parallel} \sum_i (n_{i\downarrow} - n_{i\uparrow})$$

Zeeeman Field

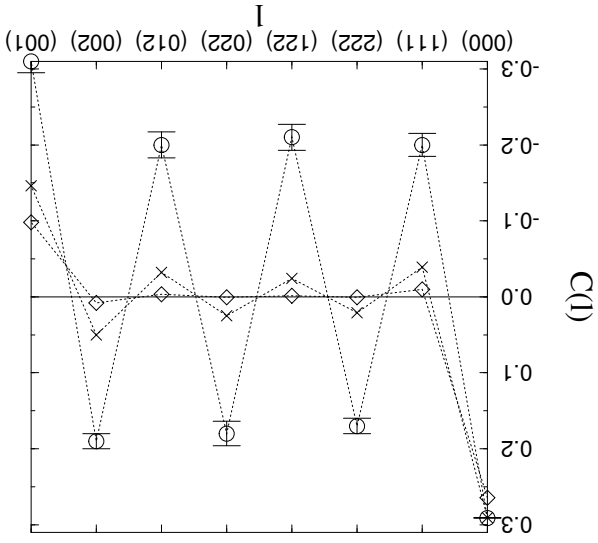
# HUBBARD HAMILTONIAN- BASIC PHYSICS

(NO DISORDER OR ZEEEMAN FIELD)

Mott Insulator at half-filling  
( $\rho = 1 e_-$  per site)



Antiferromagnetic  
spin correlations



Away from half-filling: paramagnetic metal (d-wave superconductor?)  
Stripes (charge inhomogeneities)?  
 $U$  very large: ferromagnetic phases.



# HUBBARD HAMILTONIAN-BASIC PHYSICS

WITH DISORDER (AND ZEEMAN FIELD)



No interactions ( $U = 0$ )

Anderson Insulator

With interactions ( $U \neq 0$ )

Delocalize electrons

Zeeman field: Reduce  $U$ , return to insulator

# DETERMINANT QUANTUM MONTE CARLO

## Basic Features

Exact Treatment of interactions, disorder, ...

Can measure any finite  $T$  quantity  $\langle c_{\uparrow}^{\dagger} c_{\uparrow}^{\dagger} c_{\downarrow}^{\dagger} c_{\downarrow}^{\dagger} \dots c_{k\sigma_3} c_{l\sigma_4} \dots \rangle$

Dynamics (real time) response more difficult (analytic continuation)  
Systems of up to  $\approx 4 \times 10^2$  electrons

In some models, down to zero  $T$ , in others  $T > 0.02 W$ .

## Technical Details

Path integral for partition function  $Z = e^{-\beta H}$

Interaction terms decoupled with Hubbard-Stratonovich field  $x(\tau)$   
Non-interacting electrons moving in (classical) auxiliary field

Integrate out the electrons analytically

$$Z = \int \mathcal{D}x(\tau) \det M_{\downarrow}(x) \det M_{\uparrow}(x)$$

Monte Carlo sampling over this field

Eliminate 'Trotter error':  $\beta = L\Delta\tau$  by taking  $\Delta\tau \rightarrow 0$ .

# OBSERVABLES

## Kinetic Energy

$$\langle - \sum_{\langle i,j \rangle \sigma} t_{ij} (c_{i\sigma}^\dagger c_{j\sigma} + c_{j\sigma}^\dagger c_{i\sigma}) \rangle$$

Potential Energy/Local moment

$$\langle (n_{i\downarrow} - \frac{1}{2})(n_{i\uparrow} - \frac{1}{2}) \rangle = \frac{1}{4} - \langle (n_{i\downarrow} - n_{i\uparrow})^2 \rangle$$

Compressibility

$$\kappa = \partial n / \partial \mu$$

Real space charge, spin, pairing correlations / structure factors

$$n_{i1+j1} = c_{i\downarrow}^\dagger c_{i\downarrow} + c_{i\uparrow}^\dagger c_{i\uparrow}$$

$$\langle n_{i1+j1} \rangle$$

$$m_{i1+j1} = c_{i\downarrow}^\dagger c_{i\uparrow}$$

$$\langle m_{i1+j1} \rangle$$

$$\Delta_{i1+j1} = c_{i\downarrow}^\dagger c_{i\uparrow}$$

$$\langle \Delta_{i1+j1} \rangle$$

## Current-current correlation function

$$\sum_{\beta} \int_0^1 d\tau \langle j_x(\mathbf{1}, \tau) j_x(0, 0) \rangle e^{i\mathbf{q} \cdot \mathbf{1}} e^{-i\omega_n \tau} = \sum_{\sigma} \left[ e^{H\tau} i\tau \sum_{\sigma} (c_{\dagger}^{1+\hat{x}, \sigma} c_{1, \sigma} - c_{\dagger}^{1, \sigma} c_{1+\hat{x}, \sigma}) \right] e^{-H\tau} j_x(\mathbf{1}, \tau)$$

## Conductivity

$$\sigma_{\text{dc}} = \frac{\pi}{\beta^2} \chi(\tau = \beta/2)$$

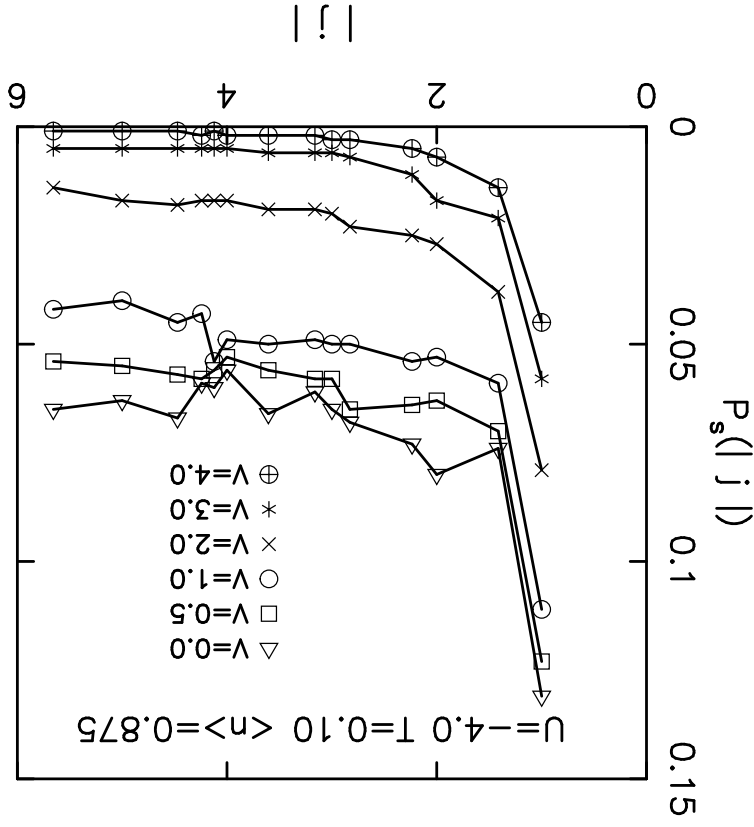
# EFFECT OF DISORDER ON PAIR CORRELATIONS IN THE ATTRACTIVE HUBBARD MODEL

$\Delta_{\mu}=0$ : long range pair correlations (SC) at low  $T$ .

$$P_s^j = \langle \Delta_s^{l+j} \Delta_s^l \rangle$$

$$\Delta_{s\uparrow} = c_{l\uparrow}^\dagger c_{l\uparrow}^\dagger$$

$\Delta_{\mu} \neq 0$ : Pair correlations are driven to zero.



# Longitudinal Current-Current Correlation Function

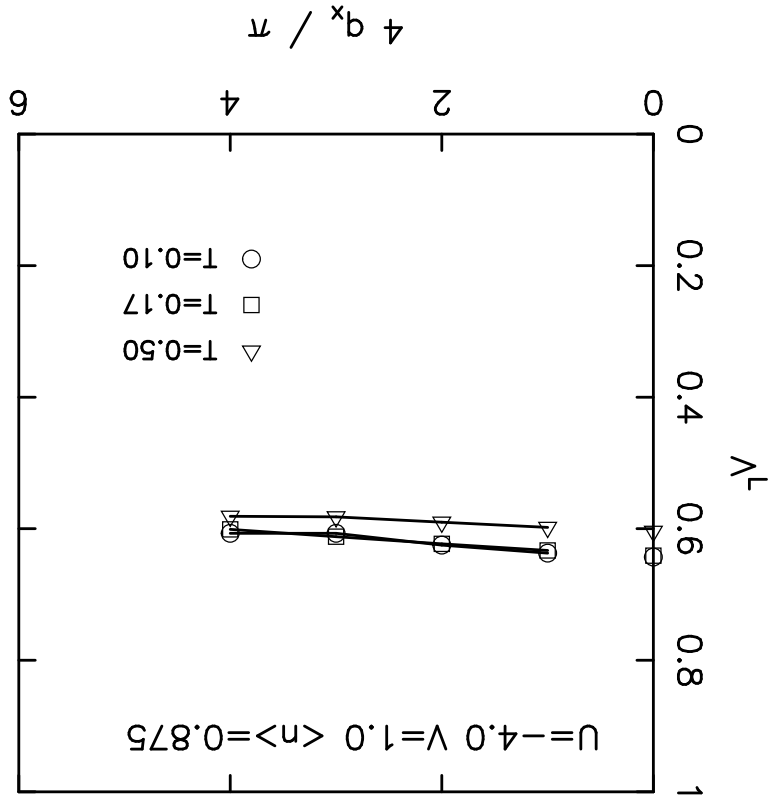
Current-current correlation function:

$$V_{xx}(\mathbf{q}; i\omega_n) = \sum_{\beta} \int_0^{\beta} d\tau \langle j_x(\mathbf{l}, \tau) j_x(0, 0) \rangle e^{i\mathbf{q} \cdot \mathbf{l}} e^{-i\omega_n \tau},$$

$$j_x(\mathbf{l}, \tau) = e^{H\tau} \left[ \sum_{\sigma} i\tau (c_{\mathbf{l}+\hat{x},\sigma}^{\dagger} c_{\mathbf{l},\sigma} - c_{\mathbf{l},\sigma}^{\dagger} c_{\mathbf{l}+\hat{x},\sigma}) \right] e^{-H\tau}.$$

The longitudinal part must satisfy the equality,

$$N_T \equiv \lim_{q_x \rightarrow 0} N_{xx}(q_x, q_y = 0; i\omega_n = 0) = -K_x.$$

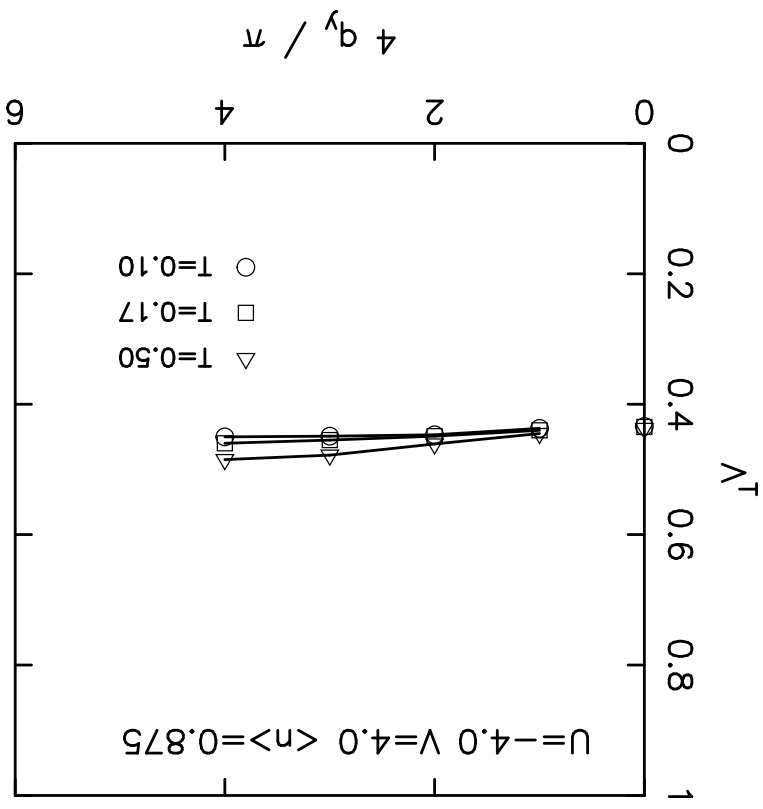
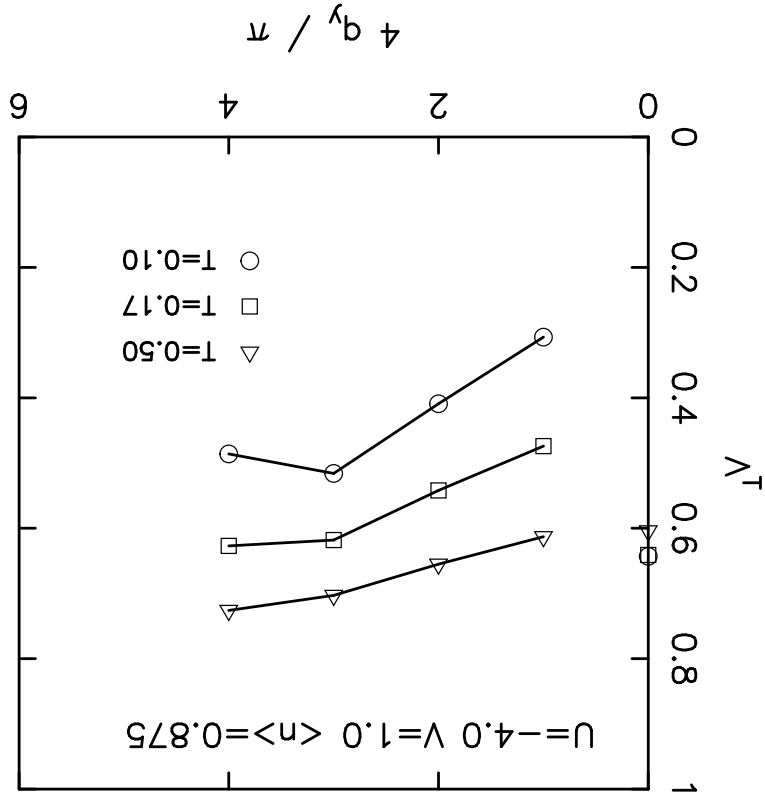


## Transverse Current-Current Correlation Function

The transverse part measures the superfluid stiffness,

$$V_T \equiv \lim_{q_y \rightarrow 0} V_{xx}(q_x = 0, q_y; i\omega_n = 0)$$

$$\rho_s = [V_T - V_T^x] = [K^x - V_T^x].$$



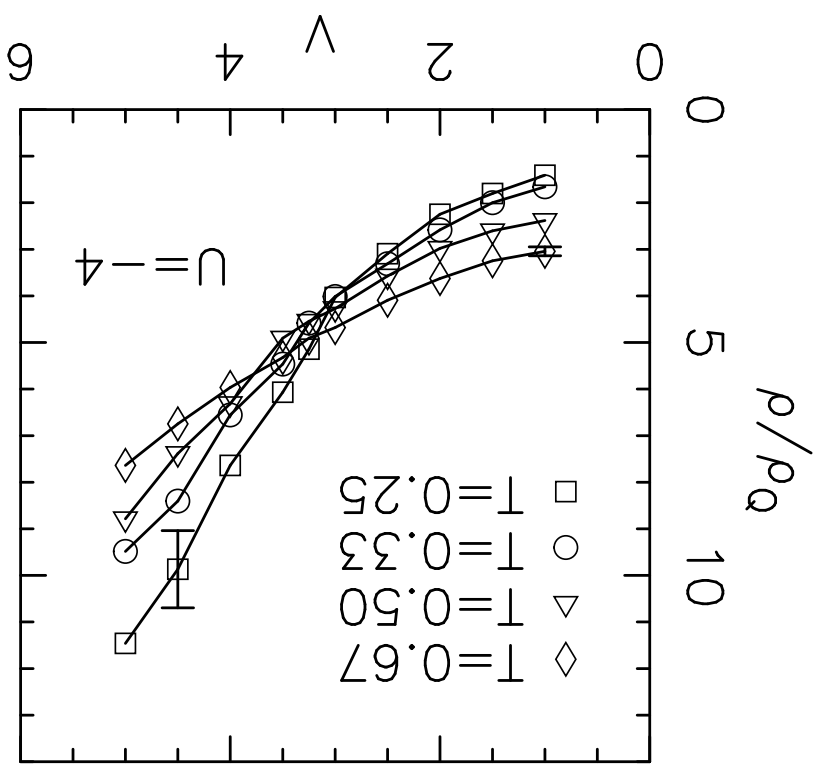
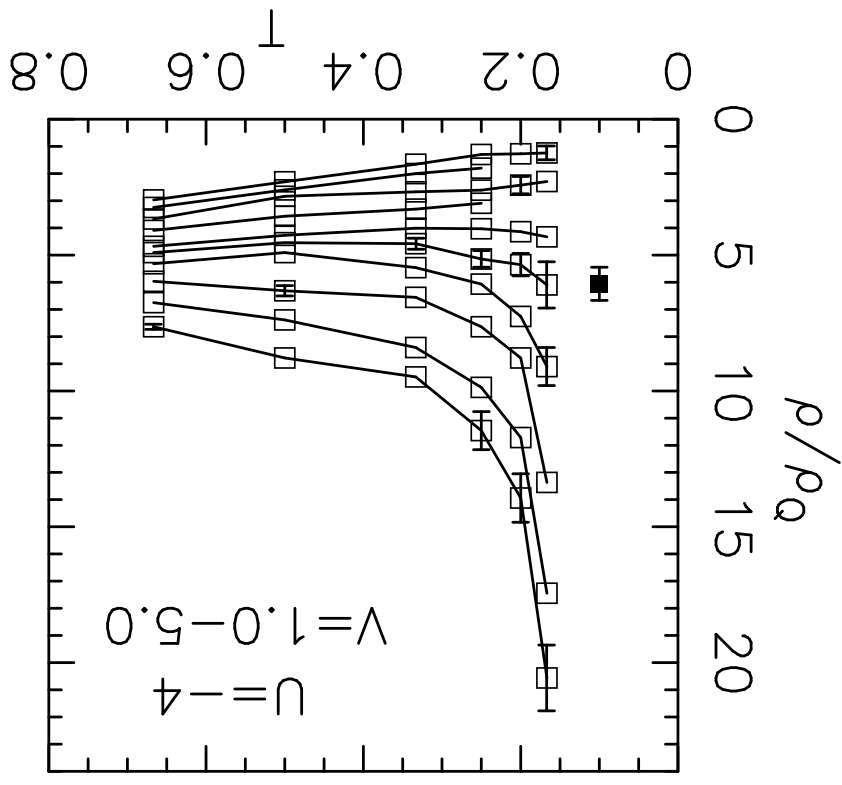


# Transport Evidence for the Superconductor-Insulator Phase Transition

$$\Lambda(\tau) = \int_{+\infty}^{-\infty} d\omega \frac{\exp(-\omega\tau)}{\exp(-\omega\tau) + 1} \frac{\pi}{\tau} \text{Im}\Lambda(\omega)$$

In the normal state,  $\text{Im}\Lambda(\omega) \sim \omega\sigma_{dc}$  at low frequencies,

$$\sigma_{dc} = \beta^2/\pi \quad \Lambda(\tau = \beta/2).$$



# REPULSIVE HUBBARD MODEL

Effect of Interactions on the Anderson Insulator

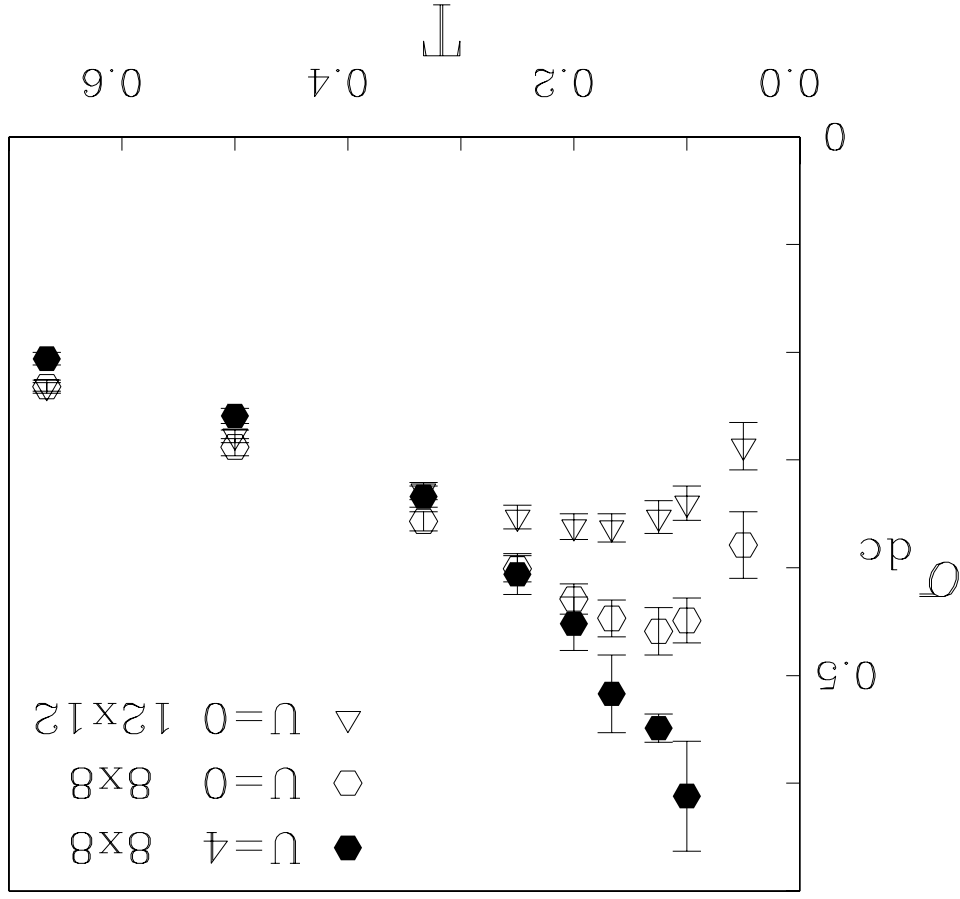
$$H = - \sum_{\langle i,j \rangle \sigma} t_{i,j} c_{i\sigma}^\dagger c_{j\sigma} + c_{i\sigma}^\dagger c_{j\sigma} + c_{j\sigma}^\dagger c_{i\sigma}$$

$$1 - \Delta_t > t_{i,j} > 1 + \Delta_t$$

When  $U$  is turned on, conductivity rises as  $T$  is lowered.

$$\Delta_t = 2$$

$$\rho = 1/2$$

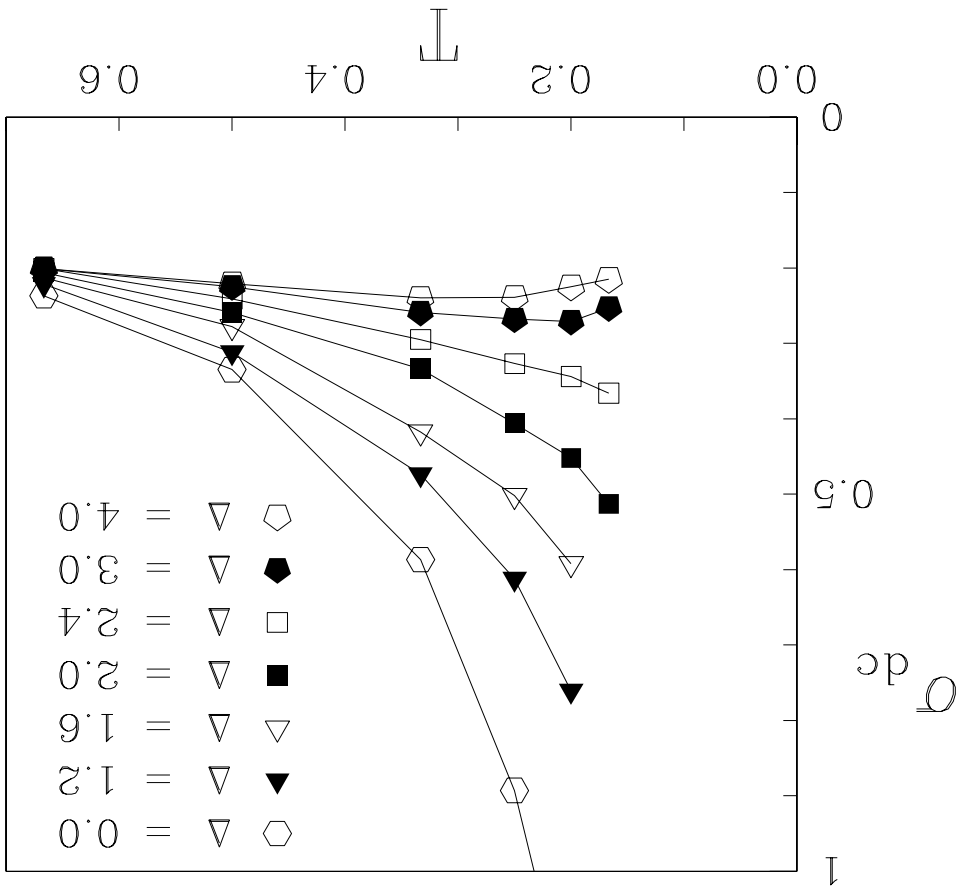


## Effect of Increased Disorder on the Metal

• Increase disorder strength in metallic phase.

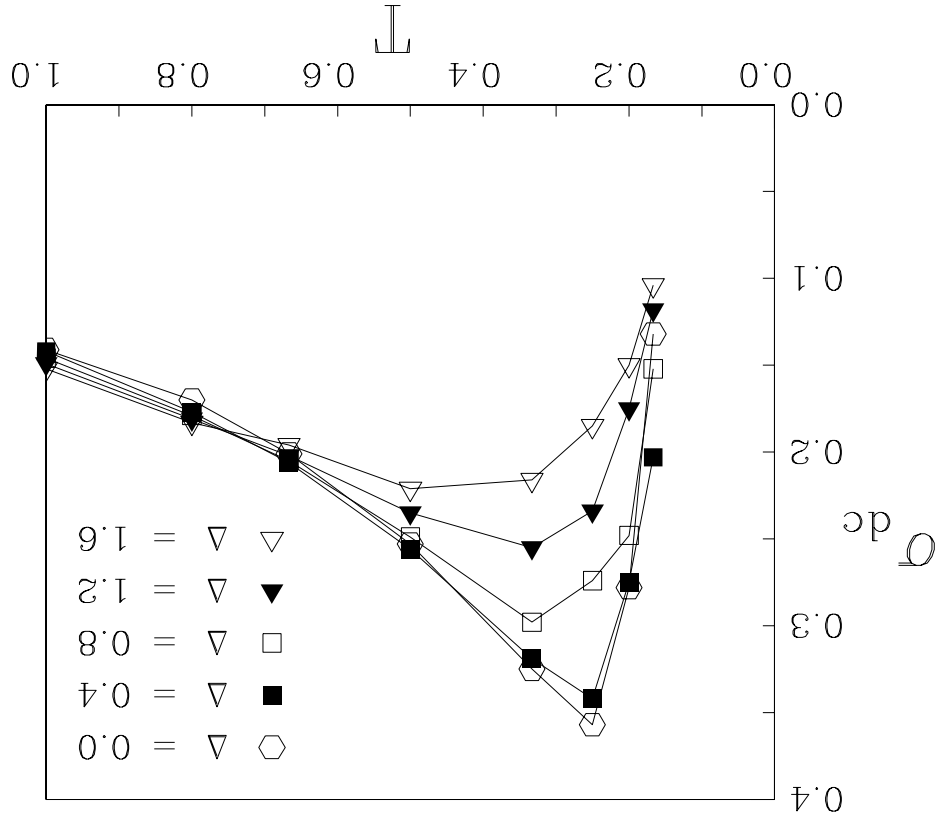
$$H = - \sum_{\langle i,j \rangle \sigma} t_{i,j} (c_{i\sigma}^\dagger c_{j\sigma} + c_{j\sigma}^\dagger c_{i\sigma})$$

System returns to insulating. MIT (tuned by disorder strength).



## Disordered Mott-Hubbard Insulator

We just showed: Hubbard model at **quarter filling** ( $\rho = 1/2$ ):  
Interactions cause **Anderson insulator** to go **metallic**.  
Further increase of bond disorder converts back to **insulator**.  
Interactions and disorder **compete**.  
At half-filling, ( $\rho = 1$ ) **Mott-Hubbard insulator**.  
Electrons localize to avoid double occupation. Effect of bond disorder?



Bond disorder makes the Mott-Hubbard Insulator more robust.  
Conductivity turns downward more strongly as  $T$  is lowered.  
Interactions and disorder **cooperate**.  
Bond disorder does destroy long-range antiferromagnetism.

## Particle Hole Symmetry

Bond disorder: **particle-hole symmetric**.

Bond disorder strengthens Mott-Hubbard insulator.

Site disorder

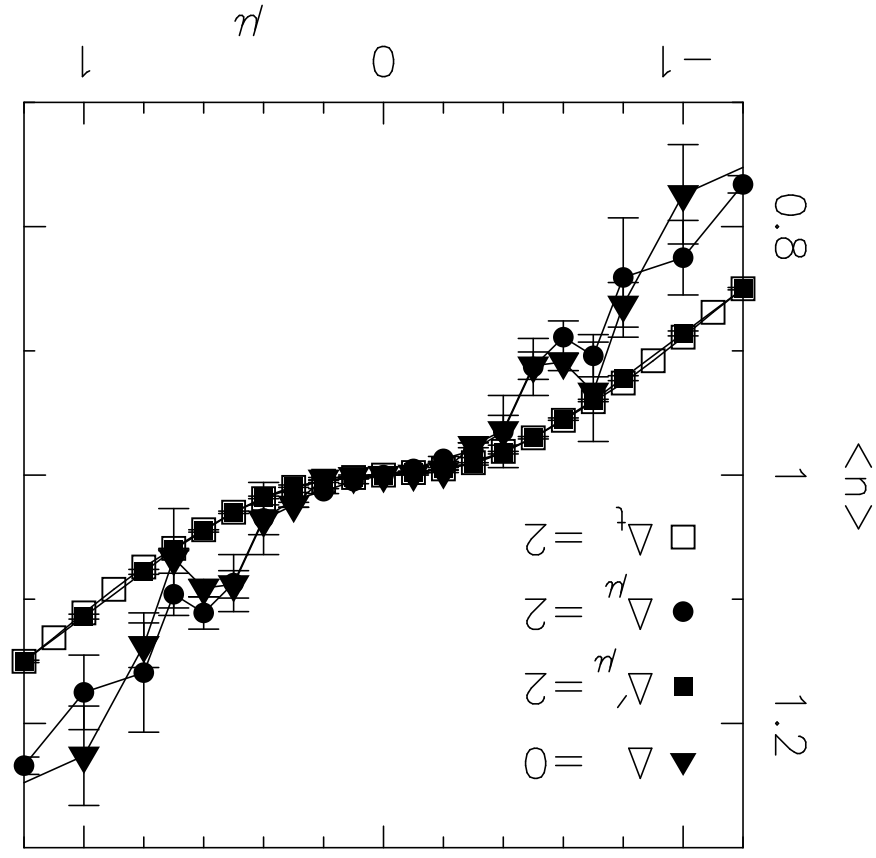
$$\sum_i \mu_i (n_{i\downarrow} + n_{i\uparrow})$$

$$-\Delta^n > \mu_i > +\Delta^n$$

not particle-hole symmetric. It destroys the Mott-Hubbard insulator.

## Another View of Particle-Hole Symmetry

Examine the Mott-Hubbard gap by evaluating  $p(\mu)$   
P-H symmetric disorder,  $\Delta_t = 2t$  and  $\Delta'_\mu = 2t$ , Mott gap enlarges.  
Canonical site disorder has little effect, for  $\Delta_\mu = 2t = U/2$ .



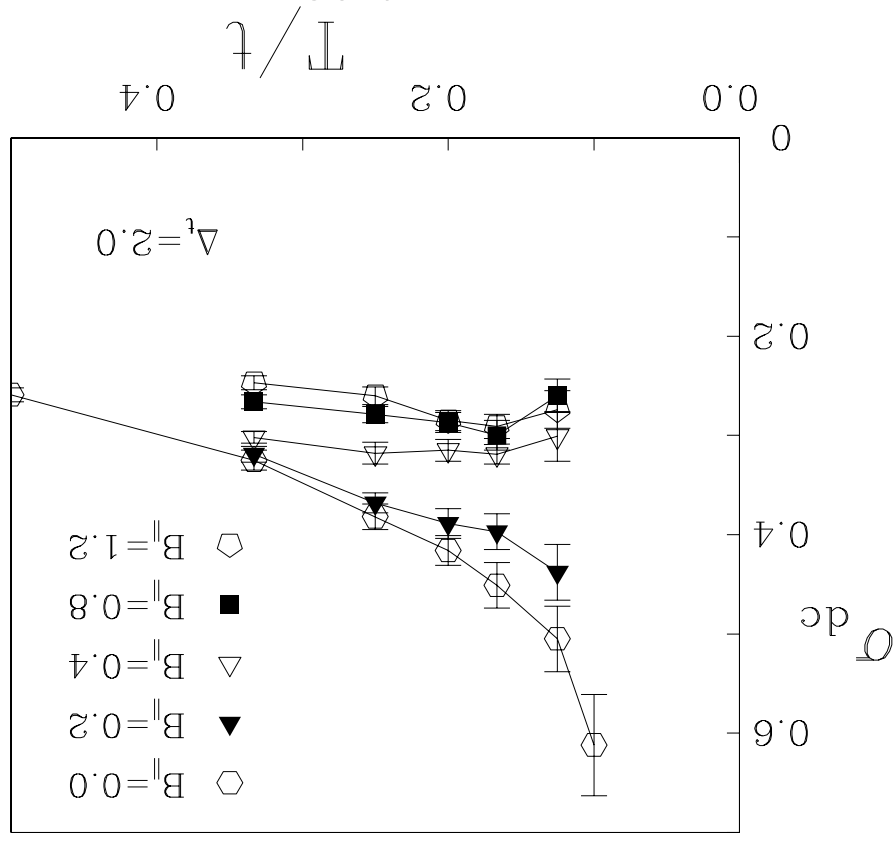
## Field Tuned Metal Insulator Transition

Hubbard Hamiltonian with a (**Zeman**) magnetic field,

$$H = - \sum_{\langle i,j \rangle \sigma} t_{i,j} (c_{i\sigma}^\dagger c_{j\sigma} + c_{j\sigma}^\dagger c_{i\sigma}) + U \sum_i n_{i\uparrow} n_{i\downarrow} + B_{\parallel} \sum_i (n_{i\downarrow} - n_{i\uparrow})$$

As  $B_{\parallel}$  is turned on, the metallic phase is destroyed.

**Simple picture:** spin polarization reduces effective interaction  $U$ .





## Location of Critical Point

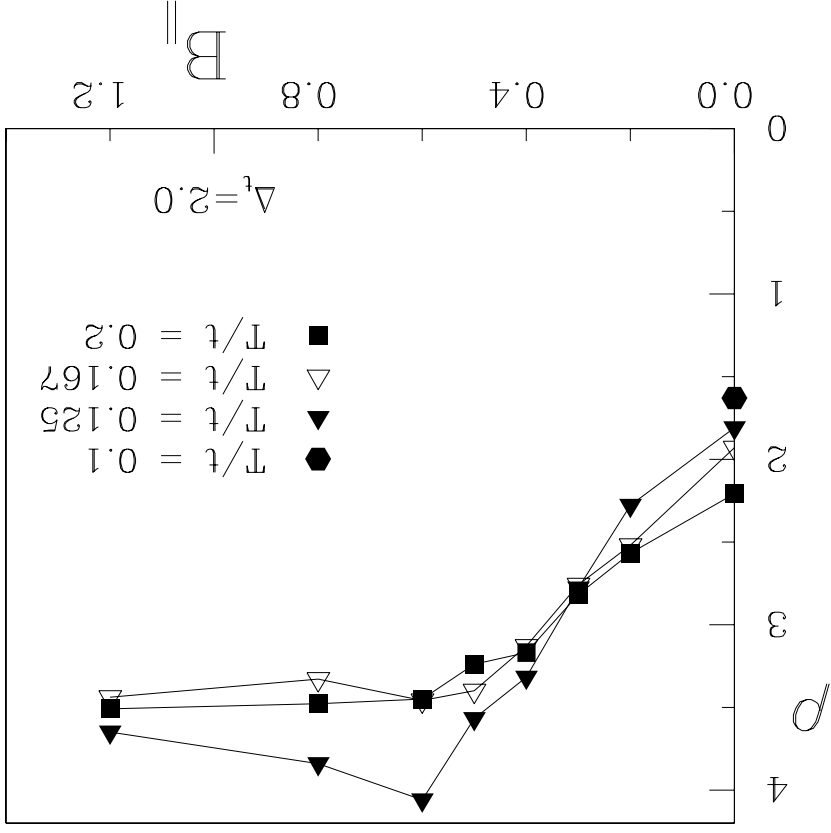
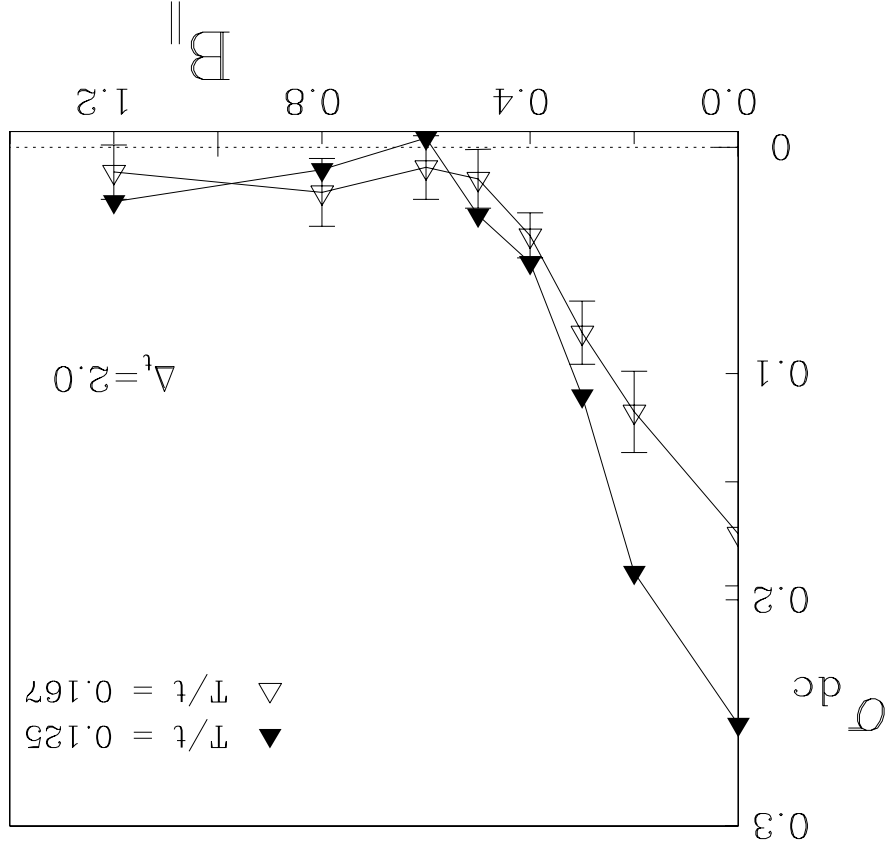
Large  $B_{\parallel}$  and nonzero disorder: conductivity  $\sigma_{dc}$  should vanish.

(Effectively, no interactions).

Subtract large  $U$  piece of  $\sigma_{dc}$  to correct for finite  $N$  and  $T$ .

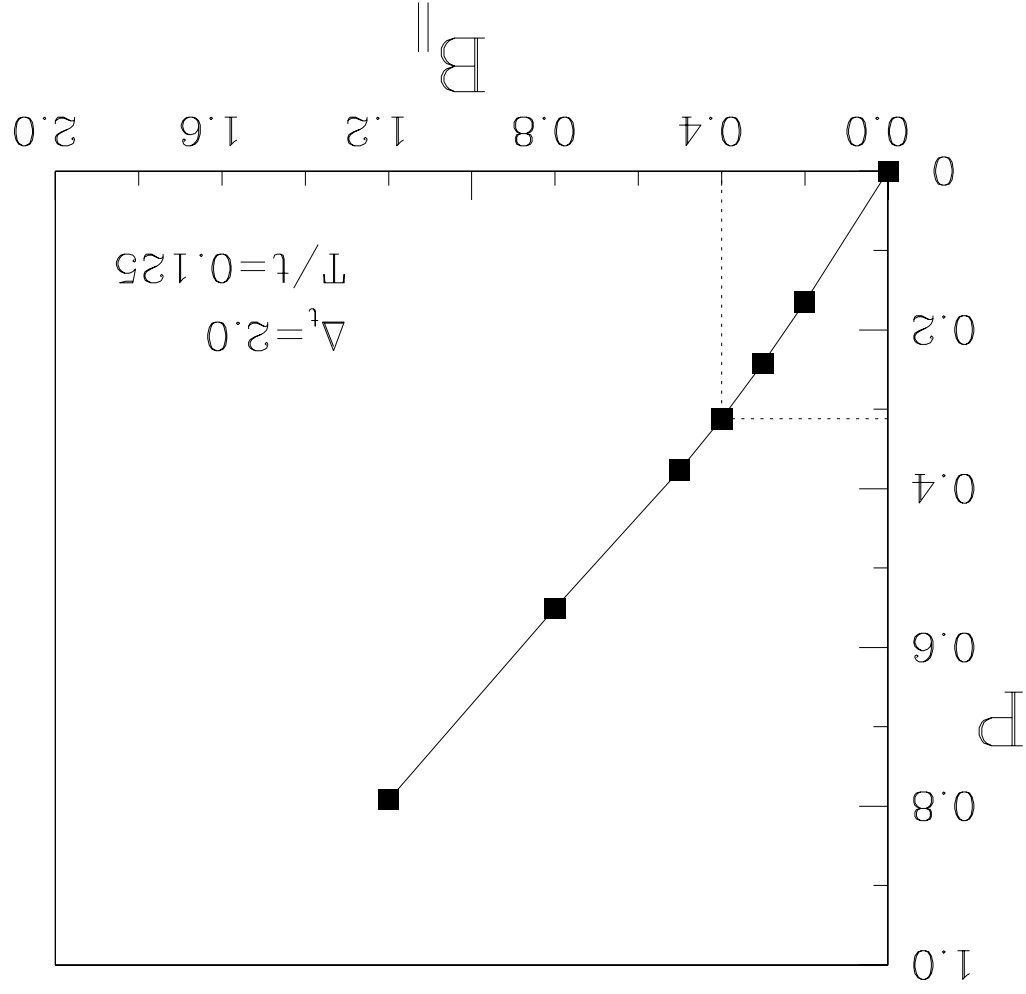
$\delta\sigma_{dc} \rightarrow 0$  for  $B_{\parallel} \approx 0.4 t$ .

Alternatively, look at crossing of  $\rho$  vs.  $B_{\parallel}$ .



Resistivity Saturation occurs below point of full spin polarization.  $\Delta_t = 2.0 t$  is fairly close to critical value  $\Delta_t^{\text{(crit)}} = 2.4 t$  where bond

disorder destroys metallic phase. Zeeman field does not need to be very big to drive to insulator. In particular, get insulator well before full spin polarization.



## Conclusions

QMC shows clear evidence for MIT in the disordered Hubbard model

\* As a function of interaction strength  $U$

\* As a function of degree of disorder

\* As a function of magnetic field

\* Field-driven MIT occurs prior to full spin polarization

\* Particle-Hole symmetry appears to play an important role